

Amplifier Transistor

NPN Silicon

MPS6428

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

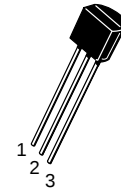
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

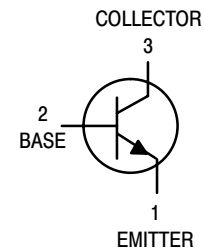
Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	50	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$)	I_{CES}	—	0.025	μA
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	0.01	μA
Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	0.01	μA



**CASE 29–04, STYLE 1
TO–92 (TO–226AA)**



MPS6428

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 0.01\text{ mAdc}$) ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 0.1\text{ mAdc}$) ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 1.0\text{ mAdc}$) ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 10\text{ mAdc}$)	h_{FE}	250 250 250 250	— 650 — —	—
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0.5\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)	$V_{CE(sat)}$	— —	0.2 0.6	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	0.56	0.66	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	700	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	3.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	8.0	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	3.0	30	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	2.0	20	$\times 10^{-4}$
Small–Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	200	800	—
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	5.0	50	μmhos

NOISE FIGURE/TOTAL NOISE VOLTAGE CHARACTERISTICS

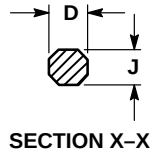
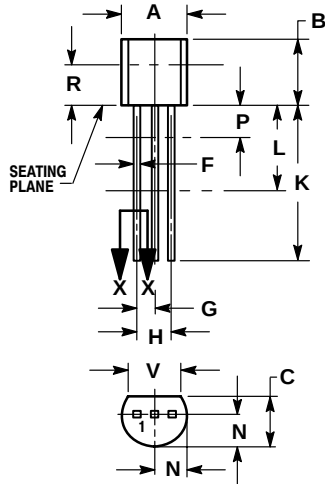
	NF Max (1)	VT	NF Max (2)	VT	NF Max (3)	VT	Unit
Noise Figure/Voltage ($V_{CE} = 5.0\text{ V}$, $I_C = 0.1\text{ mA}$, $T_A = 25^\circ\text{C}$)	7.0	18.1	6.0	5700	3.5	4.3	dB, nV

1. $R_S = 10\text{ k}\Omega$, BW = 1.0 Hz, $f = 100\text{ Hz}$
2. $R_S = 50\text{ k}\Omega$, BW = 15.7 kHz, $f = 10\text{ Hz}–10\text{ kHz}$
3. $R_S = 500\text{ }\Omega$, BW = 1.0 Hz, $f = 10\text{ Hz}$

MPS6428

PACKAGE DIMENSIONS

CASE 029-04
(TO-226AA)
ISSUE AD



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
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